

11. The method of claim 10, wherein a portion of the metal structure has a dimension less than about 0.25 micron.

12. A method for making a semiconductor device, comprising:

providing a metal structure on a substrate, the metal structure comprising tungsten and a portion of the metal structure having a dimension greater than about 1 micron; and

providing an insulating layer over the metal structure;

providing a capping structure over the insulating layer; and

annealing the resulting structure;

wherein the capping structure and annealing decreases peeling of the metal structure when heated.

13. A method for making a semiconductor device, comprising:

providing a metal structure on a substrate, the metal structure comprising tungsten and a portion of the metal structure having a dimension greater than about 1 micron; and

providing an insulating layer over the metal structure;

providing a capping structure over the insulating layer; and

annealing the resulting structure;

wherein the annealing decreases peeling of the metal structure when heated.--

#### REMARKS

Applicants hereby submit this Preliminary Amendment in response to the Notice of Missing Parts (the "Notice"). The Notice noted that the Office had not received several items that were originally filed, including page 16 of the specification and the filing fee.